

Notice of References Cited	Application/Control No. 09/045,118	Applicant(s)/Patent Under Reexamination SUZUKI ET AL.	
	Examiner Michelle Estrada	Art Unit 2823	Page 1 of 1

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*	B	US-5,440,157	08-1995	Imai et al.	257/310
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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.